



# PerF±T<sup>™</sup> Power Transistor

#### **FEATURES**

- Ultra-low On-resistance
- 100% UIS and Rg tested
- RoHS Compliant
- Halogen-Free according to IEC 61249-2-21

#### **APPLICATIONS**

- DC-DC Converters
- · Solenoid and Motor Drivers
- Load Switch

PRODUCT SUMMARY				
PARAMETER		VALUE	UNIT	
$V_{ t DS}$		40	V	
R <sub>DS(on)</sub> (max)	$V_{GS} = 10V$	5.6	0	
	$V_{GS} = 7V$	6.7	mΩ	
$Q_g$	$V_{GS} = 10V$	29	nC	

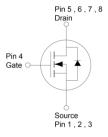












Note: MSL 1 (Moisture Sensitivity Level) per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C unless otherwise noted)				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		$V_{DS}$	40	V
Gate-Source Voltage		$V_{GS}$	±20	V
Continuous Drain Current, Silicon limited	$T_C = 25^{\circ}C$	$I_{D}$	61	Α
	$T_C = 25^{\circ}C$	I <sub>D</sub>	54	
Continuous Drain Current (Note 1)	$T_C = 100$ °C		39	Α
	$T_A = 25^{\circ}C$		16	
Pulsed Drain Current		$I_{DM}$	216	Α
Single Pulse Avalanche Current (Note 2)		I <sub>AS</sub>	21.3	А
Single Pulse Avalanche Energy (Note 2)		E <sub>AS</sub>	68	mJ
Total Dower Dissipation	T <sub>C</sub> = 25°C	$P_{D}$	34	W
Total Power Dissipation	T <sub>C</sub> = 125°C		6.8	VV
Operating Junction and Storage Temperature Range		$T_J,T_STG$	-55 to +150	°C

THERMAL RESISTANCE				
PARAMETER	SYMBOL	MAXIMUM	UNIT	
Thermal Resistance – Junction to Case	R <sub>eJC</sub>	3.7	°C/W	
Thermal Resistance – Junction to Ambient	$R_{\Theta JA}$	53	°C/W	

**Note**:  $R_{\Theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistances. The case-thermal reference is defined at the solder mounting surface of the drain pins.  $R_{\Theta JC}$  is guaranteed by design while  $R_{\Theta CA}$  is determined by the user's board design.

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PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V$ , $I_D = 1mA$	BV <sub>DSS</sub>	40			V
Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$	$V_{GS(TH)}$	2.4	3	3.6	V
Gate-Source Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$	I <sub>GSS</sub>			±100	nA
Drain-Source Leakage Current	$V_{GS} = 0V, V_{DS} = 40V$				1	μA
	$V_{GS} = 0V, V_{DS} = 40V$ $T_{J} = 125^{\circ}C$	I <sub>DSS</sub>			100	
Drain-Source On-State Resistance (Note 3)	$V_{GS} = 10V, I_D = 27A$	_		4.7	5.6	mΩ
	$V_{GS} = 7V, I_{D} = 27A$	$R_{DS(on)}$		5.3	6.7	
Forward Transconductance (Note 3)	$V_{DS} = 10V, I_{D} = 10A$	g <sub>fs</sub>		42		S
Dynamic						
Total Gate Charge	$V_{GS} = 7V, V_{DS} = 20V,$ $I_{D} = 16A$	$Q_g$		21		
Total Gate Charge		Qg		29		nC
Gate-Source Charge	$V_{GS} = 10V, V_{DS} = 20V,$	$Q_{gs}$		8.8		
Gate-Drain Charge	I <sub>D</sub> = 16A	$Q_{gd}$		5.6		
Input Capacitance		C <sub>iss</sub>		1828		
Output Capacitance	$V_{GS} = 0V, V_{DS} = 25V,$	C <sub>oss</sub>		366		pF
Reverse Transfer Capacitance	f = 1.0MHz	$C_{rss}$		35		
Gate Resistance	f = 1.0MHz	$R_g$		1.7		Ω
Switching (Note 4)						
Turn-On Delay Time		t <sub>d(on)</sub>		12		
Rise Time	$V_{GS} = 10V, V_{DS} = 20V,$	t <sub>r</sub>		49		
Turn-Off Delay Time	$I_D = 16A, R_G = 1.7\Omega$	t <sub>d(off)</sub>		25		nS
Fall Time		t <sub>f</sub>		8.9		
Source-Drain Diode						
Diode Forward Voltage (Note 3)	$V_{GS} = 0V, I_S = 27A$	V <sub>SD</sub>			1.1	V
Reverse Recovery Time	I <sub>S</sub> = 16A,	t <sub>rr</sub>		34		nS
Reverse Recovery Charge	di/dt = 100A/µs	Q <sub>rr</sub>		31		nC

#### Notes:

- 1. Package current limit.
- 2. L = 0.3mH,  $V_{GS}$  = 10V,  $R_{G}$  = 25 $\Omega$ , Starting  $T_{J}$  = 25 $^{\circ}$ C.
- 3. Pulse test: Pulse Width  $\leq$  300µs, duty cycle  $\leq$  2%.
- 4. Switching time is essentially independent of operating temperature.

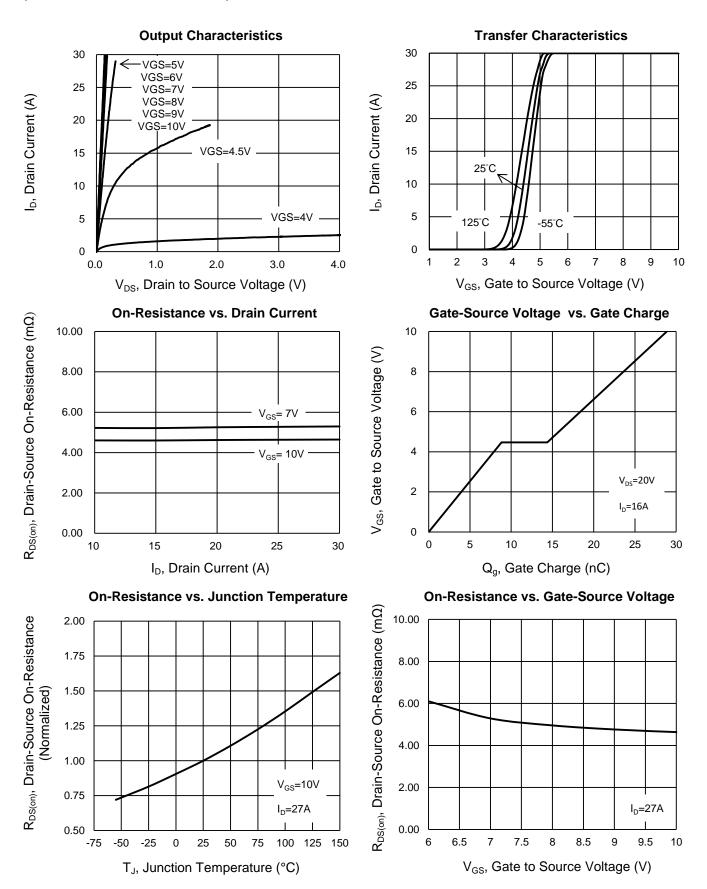
#### **ORDERING INFORMATION**

ORDERING CODE	PACKAGE	PACKING
TSM056NH04CV RGG	PDFN33	5,000pcs / 13" Reel



### **CHARACTERISTICS CURVES**

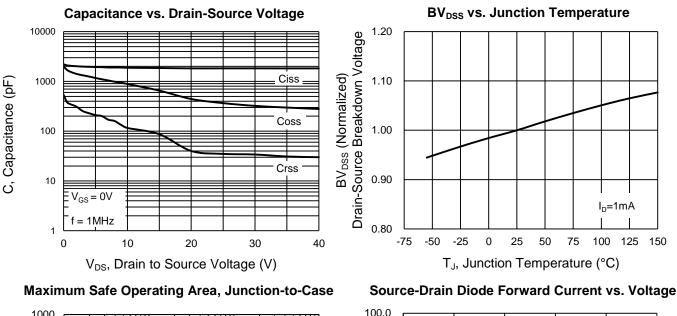
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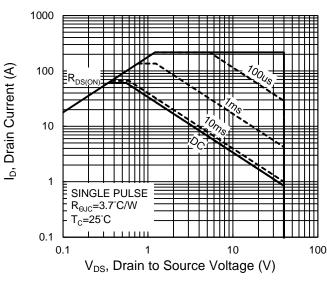


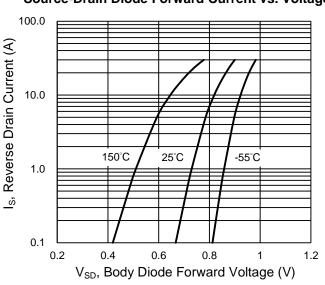


#### **CHARACTERISTICS CURVES**

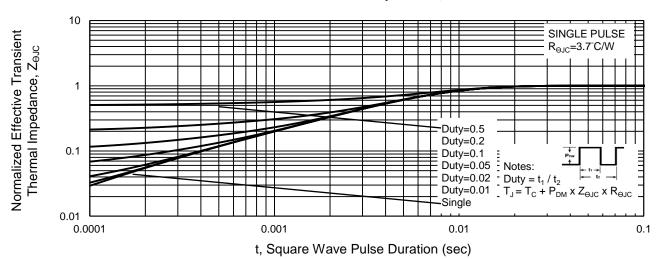
 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$ 







#### Normalized Thermal Transient Impedance, Junction-to-Case



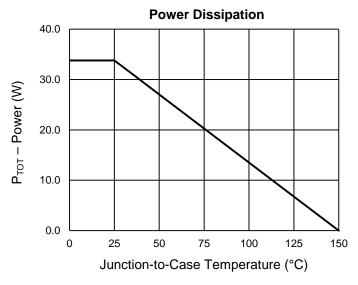
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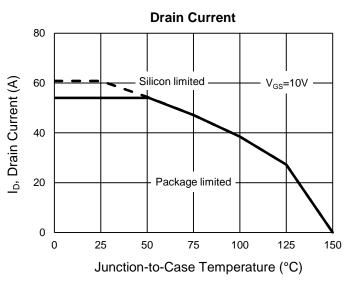




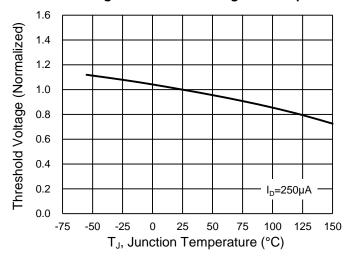
#### **CHARACTERISTICS CURVES**

(T<sub>A</sub> = 25°C unless otherwise noted)





#### Normalized gate threshold voltage vs Temperature



Version: A2207

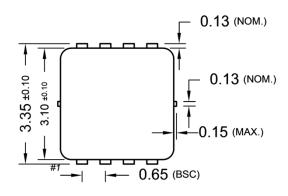
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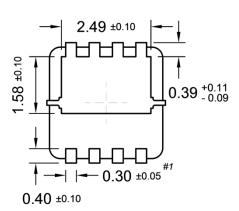


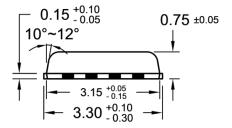


## PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

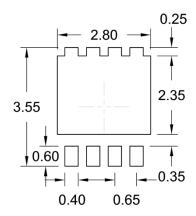
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### SUGGESTED PAD LAYOUT (Unit: Millimeters)



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#### **MARKING DIAGRAM**



Y = Year Code

**WW** = Week Code (01~52)

 $\mathbf{L}$  = Lot Code (1~9,A~Z)

**F** = Factory Code



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